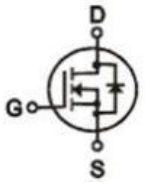
•General Description

The SGT MOSFET LH11N10S has the low $R_{DS(on)}$, low gate charge,fast switching and excellent avalanche characteristics.This device is suitable for fast charge and lighting.

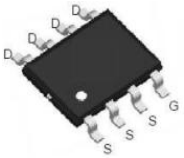


V DS =100V

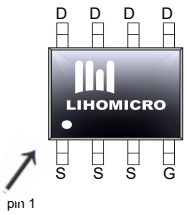
$R_{DS(ON)}$ =14mΩ

ID =11A

■ RoHS COMPLIANT



SOP-8



•Features

■Fast switching

■Low $R_{DS(on)}$ & FOM

■Low Miller Capacitance

•Application

■LED/LCD/PDP TV and monitor Lighting

■Power Supplies

■PD Charger

•Ordering Information:

Part Number	LH11N10S
Package	SOP-8
Basic Ordering Unit (pcs)	4000
Normal Package Material Ordering Code	LH11N10SS-SOP8-TAP
Halogen Free Ordering Code	LH11N10SS-SOP8-TAP-HF

•Absolute Maximum Ratings（TC =25℃）

PARAMETER	SYMBOL	Value	UNIT
Drain-Source Breakdown Voltage	BV_{DSS}	100	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current ,T_C = 25°C	I_D	11	A
Pulsed drain current (T_C = 25°C, tp limited by Tjmax)[1]	I_D pulse	70	A
Single Pulse Avalanche Energy[4]	E_{AS}	30	mJ
Power Dissipation(T_C=25℃)[2]	P_D	3.1	W
Operating Temperature	T_J	-55~+150	℃
Storage Temperature	T_{STG}	-55~+150	℃

●Electronic Characteristics

PARAMETER	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS} =0V, I_D=250uA	100	--	--	V
Gate Threshold Voltage	$V_{GS(TH)}$	V_{DS}=V_{GS},I_D=250uA	1.0	--	2.5	V
Drain-source On Resistance[3]	$R_{DS(ON)}$	V_{GS} =10V, I_D=8A	--	14	16	mΩ
		V_{GS} =4.5V, I_D=6A	--	16	23	
Drain-Source Leakage Current	I_{DSS}	V_{DS}=100V,V_{GS}=0V,T_J=25℃	--	--	1	uA
		V_{DS}=80V,V_{GS}=0V,T_J=85℃	--	--	10	
Gate-Source Leakage Current	I_{GSS}	V_{GS}=±20,V_{DS}=0V	--	--	±100	nA
Input Capacitance	Ciss	V_{GS} = 0V, V_{DS} = 50V f = 1.0MHz	--	955	--	pF
Output Capacitance	Coss		--	172	--	
Reverse transfer Capacitance	Crss		--	30	--	
Turn-On Delay time	Td(on)	V_{GS} =10V, V_{DS} = 50V, R_G=2.2Ω, I_D=10A	--	7.2	--	nS
Turn -Off Delay Time	Td(off)		--	18.4	--	
Turn-On Rise time	Tr		--	11.8	--	
Turn-Off Fall time	Tf		--	4.6	--	
Total Gate Charge	Qg	I_D =10A, V_{DS} = 50V V_{GS} = 10V	--	20	---	nC
Gate-to-Source Charge	Qgs		--	4.2	--	
Gate-to-Drain Charge	Qgd		--	5.3	---	
Continuous Diode Forward Current	I_S	--	--	--	11	A
Pulsed Diode Forward Current	I_{SM}	--	--	--	70	A
Diode Forward Voltage	V_{SD}	Tj=25°C, Is=8A V_{GS} =0V	--	--	1.3	V
Reverse Recovery Time	Trr	Is=8A, di/dt=100A/uS	--	49	--	nS
Reverse Recovery Charge	Qrr		--	89	--	nC

●Thermal Characteristics

PARAMETER	SYMBOL	MAX	UNIT
Thermal Resistance Junction-case	Rth_{JC}	1.72	℃/W
Thermal Resistance Junction-ambient[3]	Rth_{JA}	62	℃/W

Notes:

1.Repetitive Rating: Pulse width limited by maximum junction temperature.

2.Pd is based on max. junction temperature,using junction-case thermal resistance.

3.The value of R_{thA} is measured with the device mounted on 1 in 2 FR-4 board with 2oz copper,in a Still air environment with Ta=25°C.

4.V_{DD} = 50V, R_G = 25Ω, Starting T_J = 25°C.

●Typical Characteristics

Figure 1. Typ. output characteristics

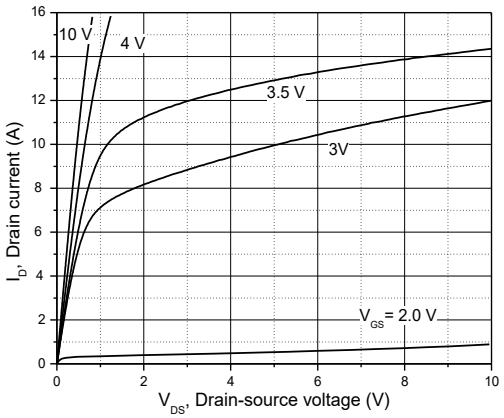


Figure 2. Typ. transfer characteristics

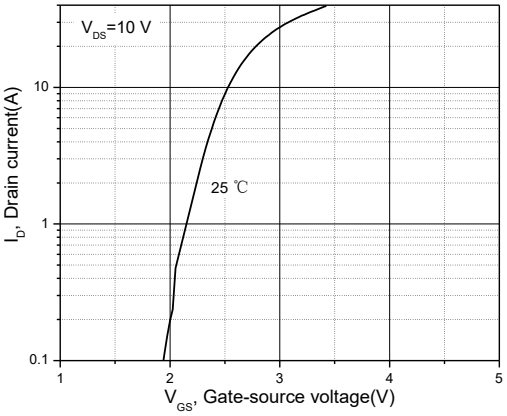


Figure 3. Typ. capacitances

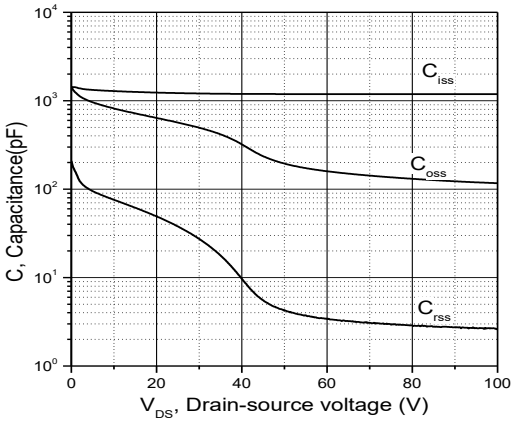


Figure 4.Typ. gate charge

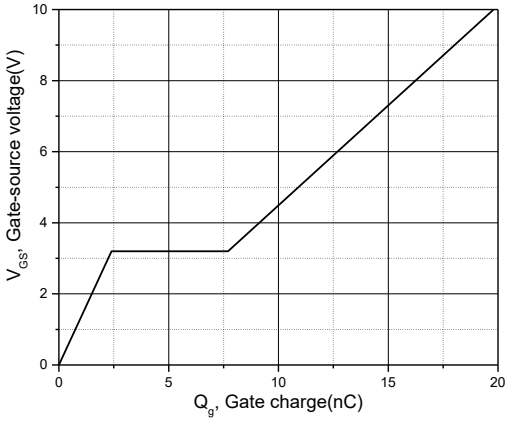


Figure 5. Drain-source breakdown voltage

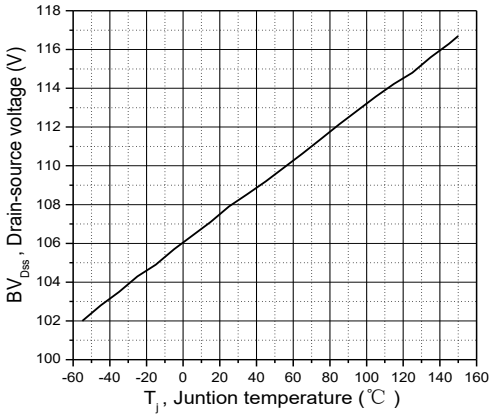
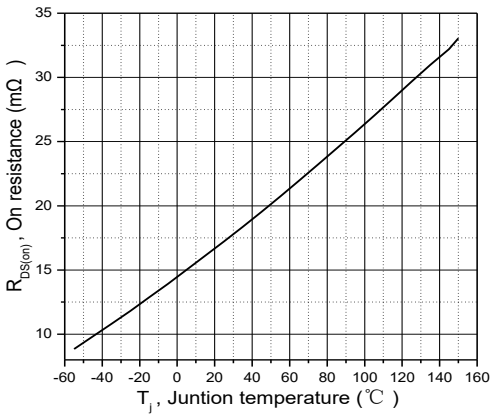


Figure 6. Drain-source on-state resistance



●Typical Characteristics(cont.)

Figure 7. Forward characteristic of body diode

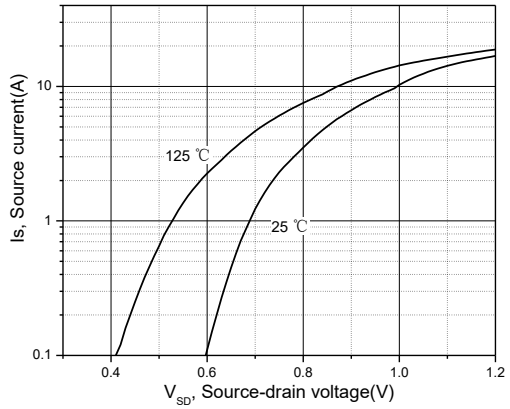


Figure 8. Drain-source on-state resistance

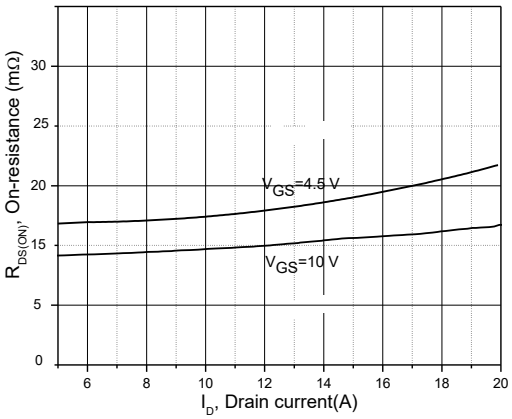
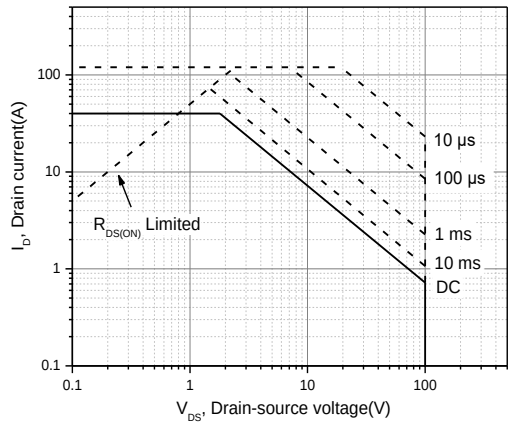


Figure 9. Safe operation area TC=25 ℃



• Test Circiuts & Waveforms

Figure 1. Gate charge test circuit & waveform

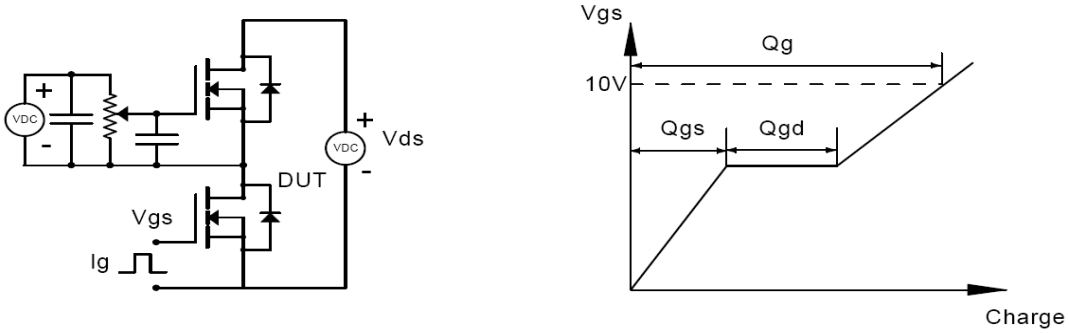


Figure 2. Switching time test circuit & waveforms

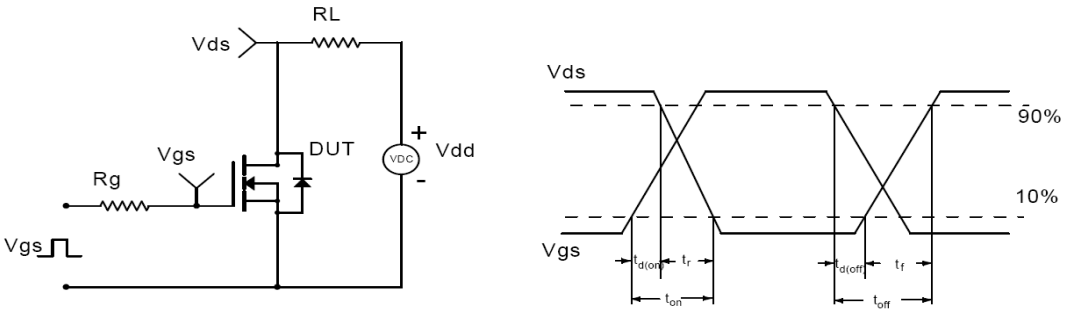


Figure 3. Unclamped inductive switching (UIS) test circuit & waveforms

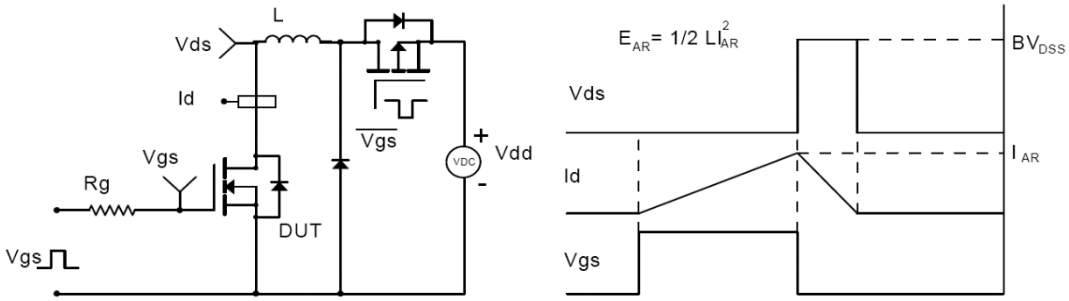
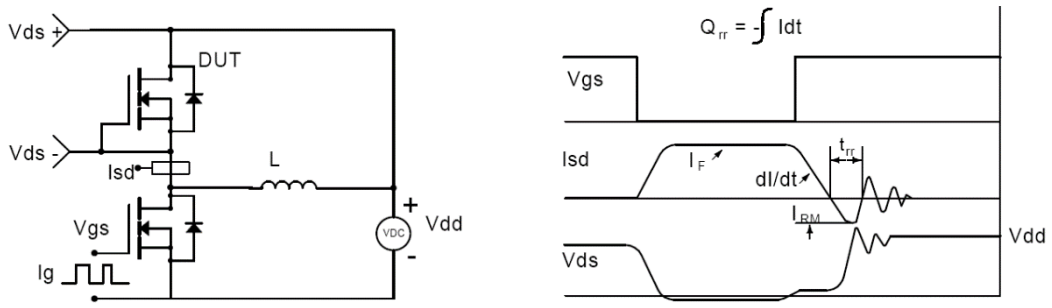


Figure 4. Diode reverse recovery test circuit & waveforms



●Dimensions（SOP-8)

UNIT:mm

SYMBOL	min	max	SYMBOL	min	max
A	1.30	1.60	e	1.27BSC	
A1	1.35	1.85	L	0.40	1.30
b	0.30	0.60			
C	0.15	0.35			
D	4.60	5.20			
E	3.70	4.10			
E1	5.70	6.30